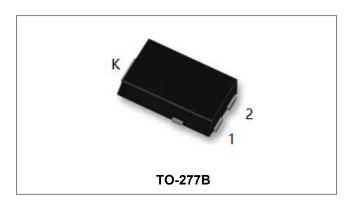






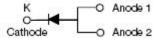
# ST12120S SCHOTTKY RECTIFIER



#### **Features**

- 150°C T<sub>J</sub> operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Trench MOS Schottky technology
- Terminals finish: 100% Pure Tin
- This is a Halogen Free Device
- . All SMC parts are traceable to the wafer lot
- · Additional testing can be offered upon request

## **Circuit Diagram**



### **Applications**

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

# **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	120	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	T <sub>C</sub> =80°C	12	А
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3ms, Half Sine pulse, T <sub>J</sub> = 25 °C	150	А

# **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	$V_{F1}$	@ 5A, Pulse, T <sub>J</sub> = 25 °C @ 12A, Pulse, T <sub>J</sub> = 25 °C	0.53 0.48	- 0.8	V
	$V_{F2}$	@ 5A, Pulse, T <sub>J</sub> = 125 °C @ 12A, Pulse, T <sub>J</sub> = 125 °C	0.50 0.58	0.7	V
Reverse Current*	I <sub>R1</sub>	$@V_R = \text{rated } V_R$ $T_J = 25  ^{\circ}\text{C}$	0.02	0.5	mA
Reverse Current*	I <sub>R2</sub>	$@V_R = \text{rated } V_R$ $T_J = 125  ^{\circ}\text{C}$	9	50	mA
Junction Capacitance	Ст	@ $V_R = 5V$ , $T_C = 25$ °C $f_{SIG} = 1MHz$	900	-	pF

<sup>\*</sup> Pulse width < 300 µs, duty cycle < 2%

- China Germany Korea Singapore United States
  - http://www.smc-diodes.com sales@ smc-diodes.com •



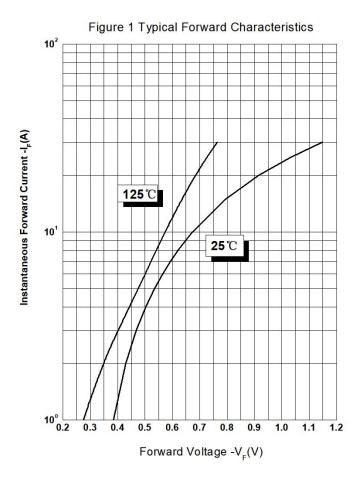




## **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	$T_{ m J}$	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	R <sub>θ</sub> JC	-	4	°C/W
Typical Thermal Resistance Junction to Ambient	$R_{\theta JA}$		70	°C/W
Approximate Weight	wt	-	0.08	g

### **Ratings and Characteristics Curves**



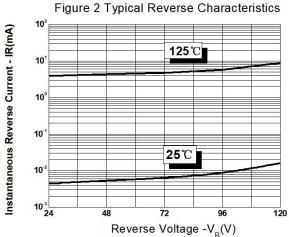
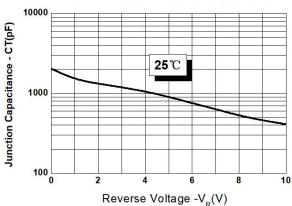


Figure 3 Typical Junction Capacitance



<sup>•</sup> China - Germany - Korea - Singapore - United States •

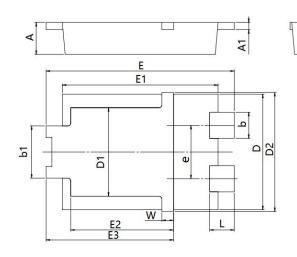
<sup>•</sup> http://www.smc-diodes.com - sales@ smc-diodes.com •

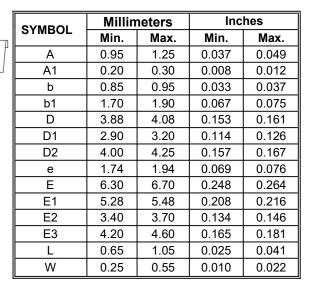




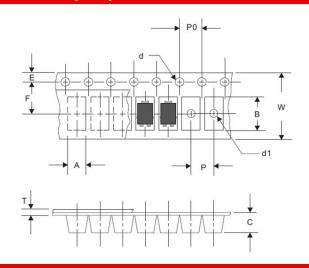


### **Mechanical Dimensions TO-277B**





### **Carrier Tape Specification TO-277B**



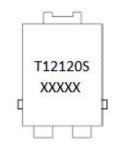
SYMBOL	Millimeters		
	Min.	Max.	
Α	4.28	4.48	
В	6.80	7.10	
С	1.30	1.50	
d	1.40	1.60	
d1	-	1.50	
E	1.65	1.85	
F	5.40	5.60	
Р	7.90	8.10	
P0	3.90	4.10	
Т	0.24	0.44	
W	11.70	12.30	

### **Ordering Information**

Device	Package	Shipping
ST12120S	TO-277B(Pb-Free)	5000pcs/ reel
ST12120STR	TO-277B(Pb-Free)	5000pcs/ reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

### **Marking Diagram**



#### Where XXXXX is YYWWL

T = Device Type
12 = Forward Current (12A)
120 = Reverse Voltage (120V)
S = Package type

YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

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